

East Search for paper no. 10

| L Number | Hits | Search Text | DB | Time stamp |
|----------|------|---|---|------------------|
| - | 5553 | ("257/296-313") or ("257/532")).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2001/04/29 23:23 |
| - | 37 | ((("257/296-313") or ("257/532")).CCLS.) and dielectric with (amorphous and crystal\$6) | USPAT | 2001/04/29 21:50 |
| - | 17 | ((("257/296-313") or ("257/532")).CCLS.) and dielectric with amorphous with crystal\$6 | USPAT | 2001/04/29 22:04 |
| - | 891 | dielectric and amorphous and crystal\$6 | EPO; JPO; DERWENT; IBM TDB | 2001/04/29 22:05 |
| - | 112 | (dielectric and amorphous and crystal\$6) and capacitor | EPO; JPO; DERWENT; IBM TDB | 2001/04/29 23:26 |
| - | 1 | jp-62046508-\$.did. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2001/04/29 22:33 |
| - | 0 | 62046508.URPN. | USPAT | 2001/04/29 22:12 |
| - | 1 | JP-62046508-\$.DID. | DERWENT | 2001/04/29 22:12 |
| - | 2 | jp-01315124-\$.did. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2001/04/29 22:34 |
| - | 1 | 1989jp-0315124.ap,prai. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2001/04/29 22:44 |
| - | 3 | 5587870.pn. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2001/04/29 22:52 |
| - | 2 | 5978207.pn. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2001/04/29 22:55 |
| - | 0 | ((("257/296-313") or ("257/532")).CCLS.) and crystalline adj silicon adj nitride with silicon adj oxide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2001/04/29 22:56 |
| - | 0 | crystalline adj silicon adj nitride and silicon adj oxide and capacitor | EPO; JPO; DERWENT; IBM TDB | 2001/04/29 22:56 |
| - | 2 | jp-05047597-\$.did. | EPO; JPO; DERWENT; IBM TDB | 2001/04/29 23:20 |
| - | 2 | jp-11121695-\$.did. | EPO; JPO; DERWENT; IBM TDB | 2001/04/29 23:22 |
| - | 2 | jp-2000252434-\$.did. | EPO; JPO; DERWENT; IBM TDB | 2001/04/29 23:22 |
| - | 5553 | ("257/296-313") or ("257/532")).CCLS. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2001/04/29 23:23 |

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|---|-----|---|---|---------------------|
| - | 0 | "JP 2000252434 A".DID. and dielectric with crystal\$6 and amorphous | USPAT | 2001/04/29 23:24 |
| - | 17 | ((("257/296-313") or ("257/532")).CCLS.) and dielectric with crystal\$6 with amorphous | USPAT | 2001/04/29 23:25 |
| - | 112 | (dielectric and amorphous and crystal\$6) and capacitor | EPO; JPO; DERWENT; IBM TDB | 2001/04/29 23:27 |
| - | 0 | ((dielectric and amorphous and crystal\$6) and capacitor) and crystalline adj silicon adj oxide | EPO; JPO; DERWENT; IBM TDB | 2001/04/29 23:28 |
| - | 0 | ((("257/296-313") or ("257/532")).CCLS.) and crystalline adj silicon adj oxide with dielectric | EPO; JPO; DERWENT; IBM TDB | 2001/04/29 23:28 |
| - | 0 | ((("257/296-313") or ("257/532")).CCLS.) and crystalline adj silicon adj oxide with dielectric | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2001/04/29 23:28 |
| - | 1 | ((("257/296-313") or ("257/532")).CCLS.) and crystalline adj silicon adj oxide | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2001/04/29 23:29 |